

Silicon NPN Power Transistors

2SC2615

DESCRIPTION

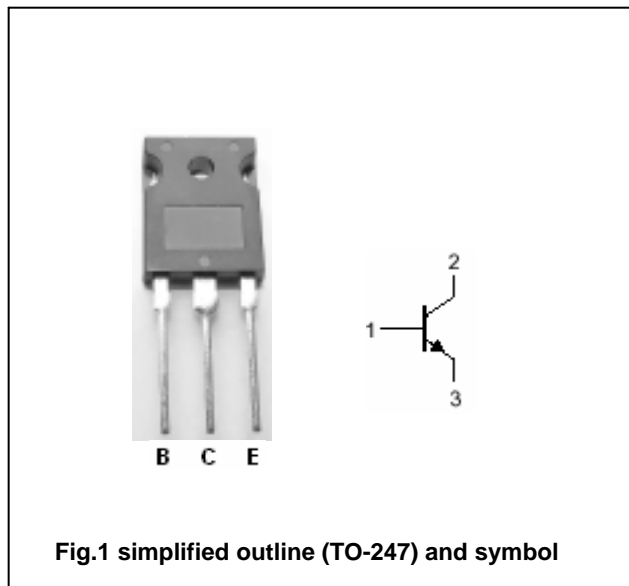
- With TO-247 package
- High voltage,high speed

APPLICATIONS

- For high voltage,high speed and high power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings($T_c=25$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current (DC)		8	A
P_C	Collector power dissipation	$T_C=25$	80	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A; I _B =0	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.8A			1.5	V
I _{CB0}	Collector cut-off current	V _{CB} =400V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =4A; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =8A; V _{CE} =5V	7			

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PACKAGE OUTLINE

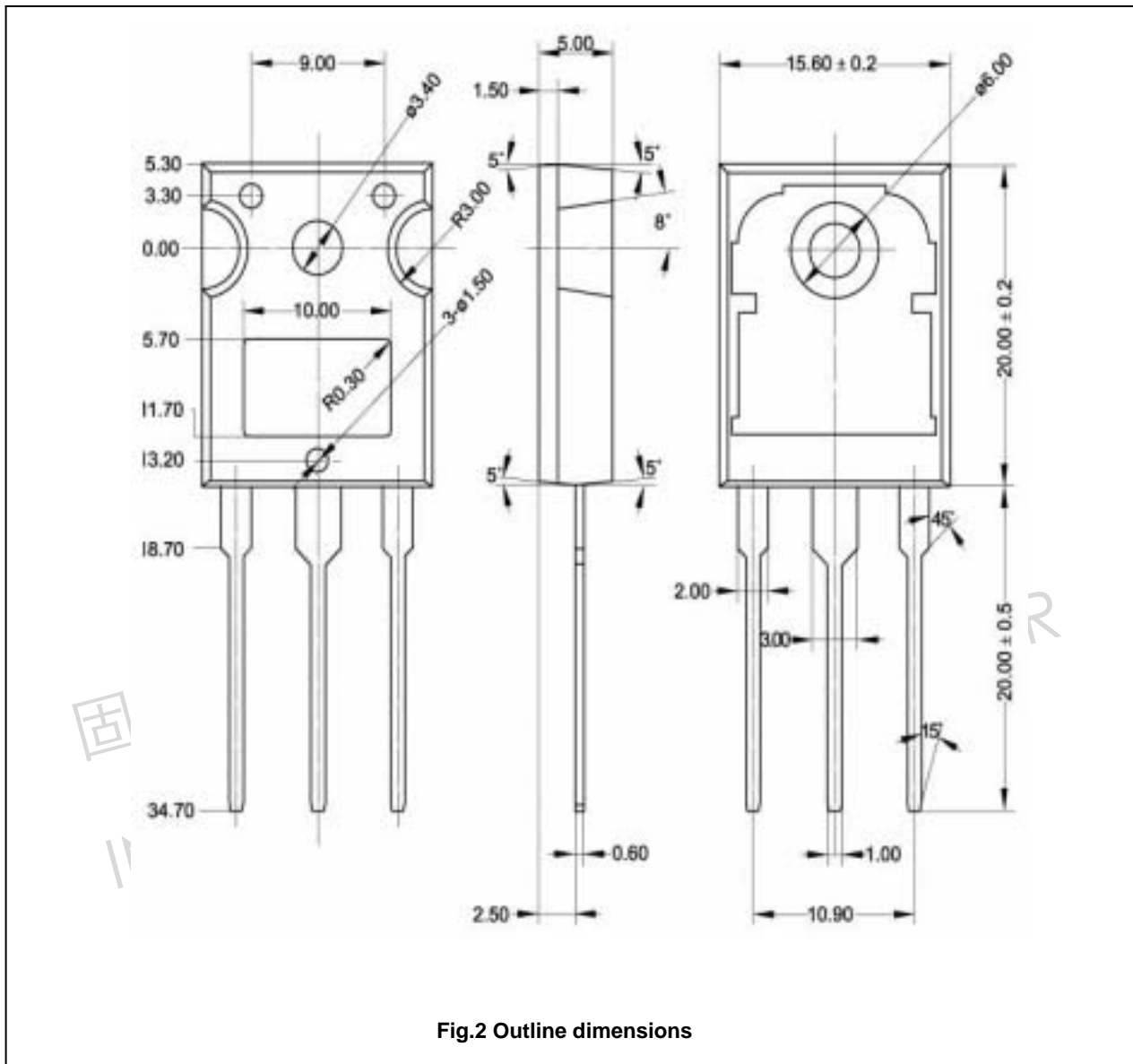


Fig.2 Outline dimensions